



Product Summary

BV _{DSS}	R _{DS(ON)} MAX	Package	I _D T _A = +25°C
	38mΩ @ V _{GS} = -10V		-4.3A
-20V	43mΩ @ V _{GS} = -4.5V	SOT23	-4.0A
	75mΩ @ V _{GS} = -2.5V		-2.8A

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Load Switch
- Power Management Functions

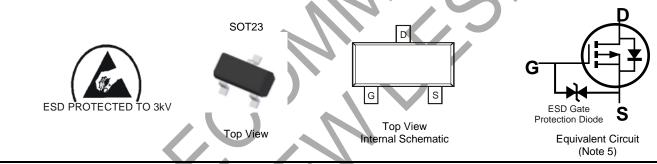
P-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 3kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (Approximate)



Ordering Information (Notes 5 & 6)

Pa	rt Number	Compliance	Case	Packaging		
DN	1P2100U-7	Standard	SOT23	3,000/Tape & Reel		
DM	P2100UQ-7	Automotive	SOT23	3,000/Tape & Reel		
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.						

No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

 Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to https://www.diodes.com/quality/.

35P = Product Type Marking Code

5. The ESD gate protection diode is only designed to protect against ESD events. No gate-source voltage greater than the maximum V_{GSS} rating (given on page 2) can be applied.

6. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

Year 2008 ~ 2017 2018 2019 2020 2021 2022 2023		
Year 2008 ~ 2017 2018 2019 2020 2021 2022 2023		
	2024	2025
Code V ~ E F G H I J K	L	М
Month Jan Feb Mar Apr May Jun Jul Aug Sep Oct	Nov	Dec
Code 1 2 3 4 5 6 7 8 9 0	N	D

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic Drain-Source Voltage Gate-Source Voltage (Note 7)			Symbol	Value	Unit	
			V _{DSS}	-20	V V	
			V _{GSS}	±10		
Continuous Drain Current (Nate 0) // 40/	Steady State	T _A = +25°C T _A = +70°C	I _D	-4.3 -3.4	А	
Continuous Drain Current (Note 9) $V_{GS} = -10V$	t<5s	T _A = +25°C T _A = +70°C	I _D	-5.5 -4.3	А	
Maximum Continuous Body Diodes Forward Current (Note 9)			ls	-2	А	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	-30	А	
Pulsed Body Diodes Forward Current (10µs Pulse, Duty Cycle = 1%)			I _{SM}	-30	А	

Thermal Characteristics

Characteristic			Symbol	Value	Unit
Total Power Dissipation (Note 8)	T _A = +25°C T _A = +70°C		PD	0.8	W
Thermal Resistance, Junction to Ambient (Note 8)	Steady State t<5s		R _{0JA}	161 96	°C/W
Total Power Dissipation (Note 9)	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$		PD	1.3 0.8	W
Thermal Resistance, Junction to Ambient (Note 9)	Steady State t<5s		R _{0JA}	99 60	°C/W
Thermal Resistance, Junction to Case (Note 9)		. (R _{0JC}	15	
Operating and Storage Temperature Range			TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 10)							
Drain-Source Breakdown Voltage	BV _{DSS}	-20		_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	IDSS		H	-1	μA	$V_{DS} = -20V, V_{GS} = 0V$	
Gate-Source Leakage	Igss		—	±10	μA	$V_{GS} = \pm 8V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 10)							
Gate Threshold Voltage	V _{GS(TH)}	-0.3		-1.4	V	$V_{DS} = V_{GS}$, $I_D = -250 \mu A$	
		-	25	38		$V_{GS} = -10V, I_D = -3.5A$	
Static Drain-Source On-Resistance	D		29	43	mΩ	$V_{GS} = -4.5V, I_D = -3A$	
Static Drain-Source On Resistance	RDS(ON)		37	75	11152	V _{GS} = -2.5V, I _D = -1A	
			47	_		$V_{GS} = -1.8V, I_D = -0.5A$	
Forward Transfer Admittance	Y _{fs}		3	-	S	$V_{DS} = -5V, I_D = -4A$	
DYNAMIC CHARACTERISTICS (Note 11)							
Input Capacitance	Ciss		216	_	рF		
Output Capacitance	Coss		90	-	pF	V _{DS} = -15V, V _{GS} = 0V f = 1.0MHz	
Reverse Transfer Capacitance	Crss		24	_	рF	1 = 1.00012	
Gate Resistnace	Rg		250	-	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
SWITCHING CHARACTERISTICS (Note 11)							
Total Gate Charge	Qg	-	9.1	—	nC		
Gate-Source Charge	Q _{gs}		1.6	_	nC	V _{GS} = -4.5V, V _{DS} = -10V I _D = -4A	
Gate-Drain Charge	Q _{gd}		2.0	_	nC	ID = -4A	
Turn-On Delay Time	t _{D(ON)}		80	_	ns		
Turn-On Rise Time	t _R		155	—	ns	$V_{DS} = -10V, V_{GS} = -4.5V,$	
Turn-Off Delay Time	t _{D(OFF)}		688	_	ns	$R_D = 2.5\Omega, R_G = 3.0\Omega$	
Turn-Off Fall Time	t _F		423	_	ns		

7. AEC-Q101 V_{GS} maximum is $\pm 9.6V.$ Notes:

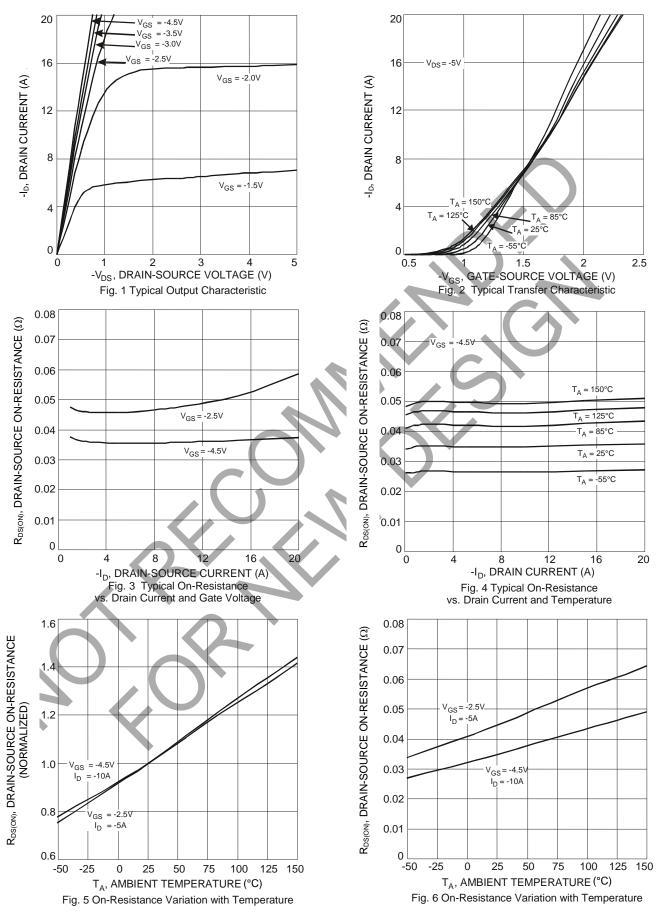
8. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 9. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.



NOT RECOMMENDED FOR NEW DESIGN USE <u>DMP2045U</u>

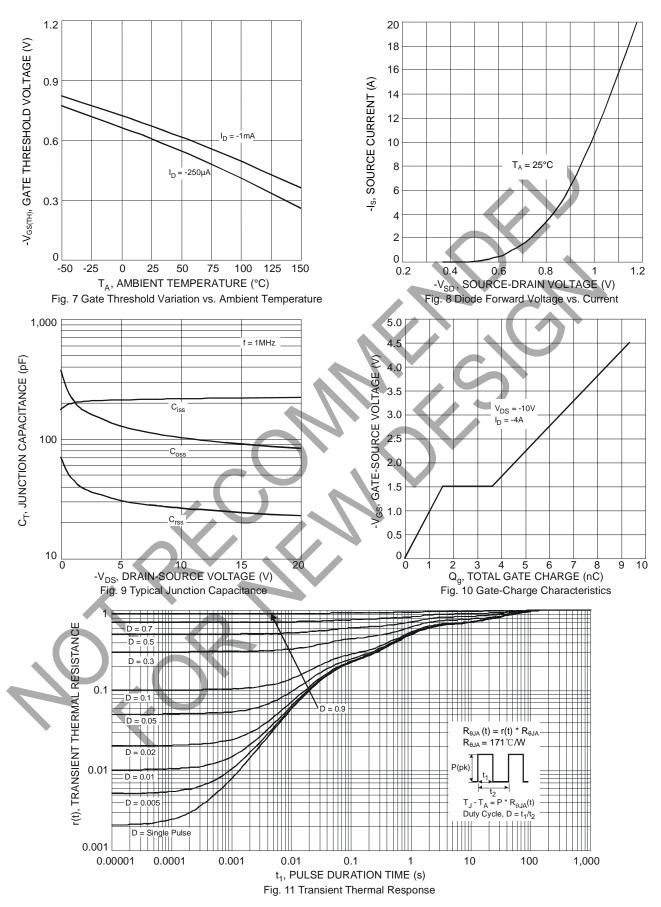
DMP2100U





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DMP2100U

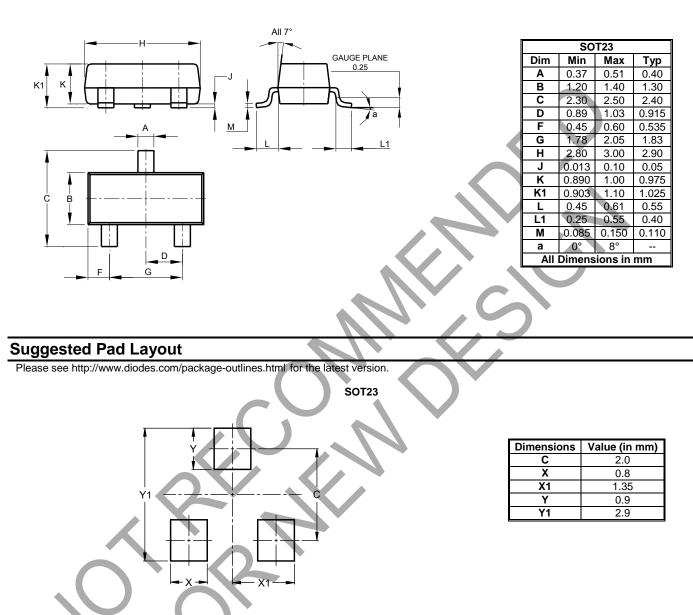




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23





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